SN65DP141 DisplayPort 线性转接驱动器

1 特性

- 支持 VESA DisplayPort 1.4a、2.0 和 eDP 1.4
- 四通道线性转接驱动器，支持高达 12Gbps 的数据速率，包括 DisplayPort RBR、HBR、HBR2、HBR3 和 UHBR10
- 与协议无关
- 透明呈现 DP 链路训练
- 与在链路上的位置无关，适用于源端、接收端和电缆应用
- 6GHz 时模拟均衡为 15dB
- 输出线性动态范围：1200mV
- 带宽：>20 GHz
- 6GHz 时的回波损耗优于 16dB
- 2.5V 或 3.3V ±5% 单电源选项
- 低功耗，2.5V V_{CC} 时每通道 80mW
- GPIO 或 I^2C 控制

2 应用

- 平板电脑
- 笔记本电脑
- 台式机
- 扩展坞

3 说明

SN65DP141 是一款与协议无关的异步、低延迟、四通道线性均衡器，该器件经过优化适用于高达 12Gbps 的数据速率并且可对电路板走线和电缆所产生的损耗进行补偿。

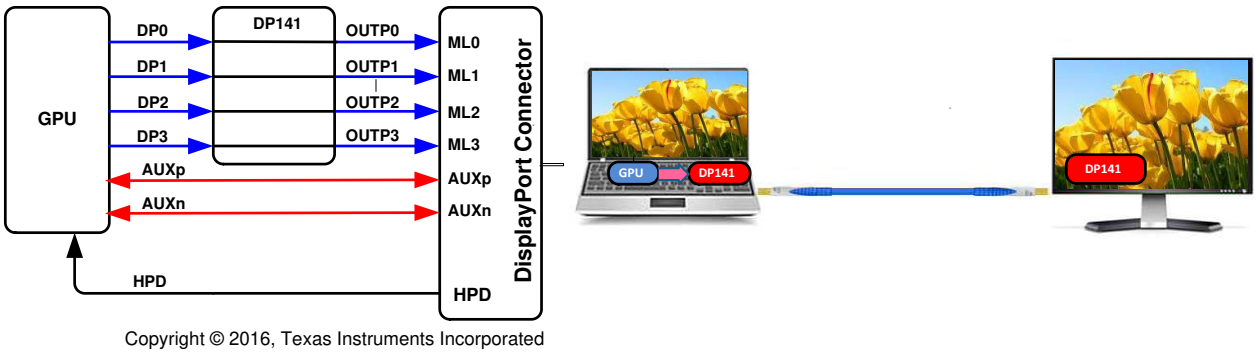
该器件透明呈现 DisplayPort (DP) 链路训练，这使得 DP 发送设备和接收设备能够执行有效的链路训练，克服了传统 *aux snooping* 转接驱动器的缺点。此外，该器件与位置无关。它可置于源设备、电缆或接收设备内，从而为总体链路预算有效提供*负损耗*分量。SN65DP141 内的线性均衡在与接收器搭配使用时还可提高链路裕度，从而实现判决反馈均衡 (DFE)。

SN65DP141 支持采用 I^2C 和 GPIO 配置对均衡、增益、动态范围进行独立通道控制。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
SN65DP141	WQFN (38)	7.00mm × 5.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化版原理图

Table of Contents

4 Revision History

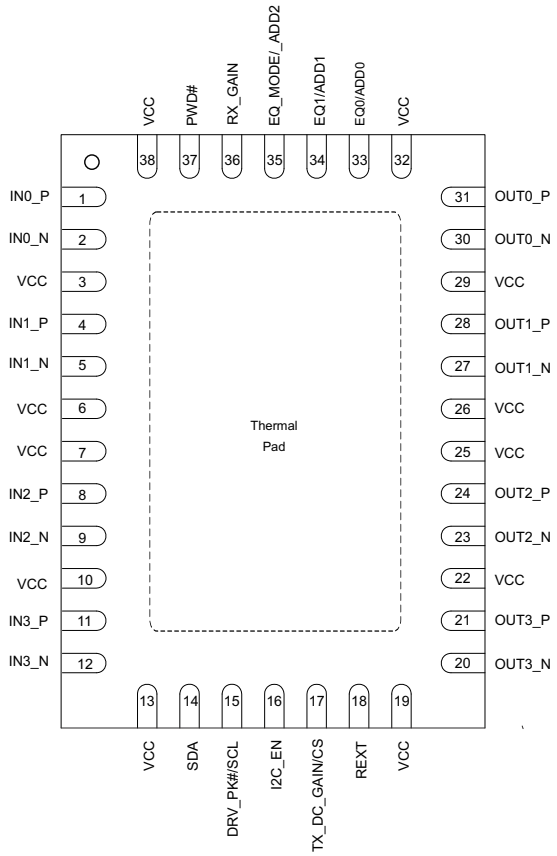
注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (September 2021) to Revision C (December 2021)	Page
• Changed the I2C_EN pin Type from *internal pull-up* to *internal pull-down*	3

Changes from Revision A (October 2016) to Revision B (September 2021)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式	1
• 将特性从：“支持 VESA DisplayPort 1.3 和 eDP 1.4”更新为：“支持 VESA DisplayPort 1.4a、2.0 和 eDP 1.4”	1
• 将特性从“包括 DisplayPort RBR、HBR、HBR2 和 HBR3”更新为“包括 DisplayPort RBR、HBR、HBR2、HBR3 和 UHBR10”	1
• Updated the DP bit rates from: RBR to HBR3 (1.6 Gbps, 2.7 Gbps, 5.4 Gbps and 8.1 Gbps ... to: RBR to UHBR10 (1.6 Gbps, 2.7 Gbps, 5.4 Gbps, 8.1 Gbps and 10.0 Gbps ⋯ in the *Overview* section	15
• Updated Operating data rate from HBR3 (8.1 Gbps) to UHBR10 (10 Gbps)	24

Changes from Revision * (February 2016) to Revision A (October 2016)	Page
• Replaced 图 9-2	25

5 Pin Configuration and Functions



It is required for the thermal pad to be soldered to ground for better thermal performance.

图 5-1. RLJ Package 38 Pins (WQFN) Top View

表 5-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	NO.		
DIFFERENTIAL HIGH-SPEED I/O			
IN0_P	1	I	Differential input, lane 0 (with 50 Ω termination to input common mode)
IN0_N	2	I	
IN1_P	4	I	Differential input, lane 1 (with 50 Ω termination to input common mode)
IN1_N	5	I	
IN2_P	8	I	Differential input, lane 2 (with 50 Ω termination to input common mode)
IN2_N	9	I	
IN3_P	11	I	Differential input, lane 3 (with 50 Ω termination to input common mode)
IN3_N	12	I	
OUT0_P	31	O	Differential output, lane 0
OUT0_N	30	O	
OUT1_P	28	O	Differential output, lane 1
OUT1_N	27	O	
OUT2_P	24	O	Differential output, lane 2
OUT2_N	23	O	
OUT3_P	21	O	Differential output, lane 3
OUT3_N	20	O	

表 5-1. Pin Functions (continued)

PIN		TYPE(1)	DESCRIPTION	
NAME	NO.			
CONTROL SIGNALS				
DRV_PK#/SCL	15	I (with 200-kΩ internal pull-up)	GPIO mode: HIGH: disable Driver peaking LOW: enables Driver 6-dB AC peaking	I²C mode: I²C CLK. Connect a 10-kΩ pull-up resistor externally.
EQ_MODE/ ADD2	35	I (with 200-kΩ Internal pull-down, 2.5 V/3.3 V CMOS)	GPIO mode: HIGH: Trace mode LOW: Cable mode	I²C mode: ADD2 along with pins ADD1 and ADD0 comprise the three bits of I²C slave address. ADD2:ADD1:ADD0:XXX
EQ0/ADD0	33	I (2.5 V/3.3 V CMOS - 3-state)	GPIO mode: Working with RX_GAIN and EQ1 to determine the receiver DC and AC gain.	I²C mode: ADD0 along with pins ADD1 and ADD2 comprise the three bits of I²C slave address. ADD2:ADD1:ADD0:XXX
EQ1/ADD1	34	I (2.5 V/3.3 V CMOS - 3-state)	GPIO mode: Working with RX_GAIN and EQ0 to determine the receiver DC and AC gain.	I²C mode: ADD1 along with pins ADD0 and ADD2 comprise the three bits of I²C slave address ADD2:ADD1:ADD0:XXX
I2C_EN	16	I (with 200-kΩ internal pull-down)	Configures the device operation for I²C or GPIO mode: HIGH: enables I2C mode LOW: enables GPIO mode	
PWD#	37	I (with 200-kΩ Internal pull-up, 2.5 V/3.3 V CMOS)	HIGH: Normal Operation LOW: Power downs the device, inputs off and outputs disabled, resets I²C	
REXT	18	I (analog)	External Bias Resistor: 1,200 Ω to GND	
RX_GAIN	36	I (2.5 V/3.3 V CMOS - 3-state)	GPIO mode: Working with EQ0 and EQ1 to determine the receiver DC and AC gain.	I²C mode: No action needed
SDA	14	I/O (open drain)	GPIO mode: No action needed.	I²C mode: I²C data. Connect a 10-kΩ pull-up resistor externally.
TX_DC_GAIN/CS	17	I (with 200-kΩ Internal pull-down, 2.5 V/3.3 V CMOS)	GPIO mode: HIGH: 6 dB DC gain for transmitter LOW: 0 dB DC gain for transmitter	I²C mode: HIGH: acts as Chip Select LOW: disables I²C interface
POWER SUPPLY				
GND Center Pad		Ground	The ground center pad is the metal contact at the bottom of the package. This pad must be connected to the GND plane. At least 15 PCB vias are recommended to minimize inductance and provide a solid ground. Refer to the package drawing (RLJ-package) for the via placement.	
VCC	3, 6, 7, 10, 13, 19, 22, 25, 26, 29, 32, 38	Power	Power supply 2.5 V ±5%, 3.3 V ±5%	

(1) I = input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	MAX	UNIT
Supply voltage range	VCC	– 0.3	4	V
Differential voltage between INx_P and INx_N	VIN, DIFF	– 2.5	2.5	V
Voltage at INx_P and INx_N,	VIN+, IN –	– 0.5	V_{CC} + 0.5	V
Voltage on control IO pins,V_{IO}		– 0.5	V_{CC} + 0.5	V
Continuous current at high speed differential data inputs(differential)	IN+, IN –	– 25	25	mA
Continuous current at high speed differential data outputs	IOUT+, IOUT –	– 25	25	mA

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. .

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
DR	Operating data rate			12	Gbps
V_{CC}	Supply voltage	2.375	2.5/3.3	3.465	V
T_C	Junction temperature	– 10		125	°C
T_A	Operating free-air temperature	– 40		85	°C
CMOS DC SPECIFICATIONS					
V_{IH}	Input high voltage	0.8 x V_{CC}			V
$V_{(MID)}$	Input middle voltage	V_{CC} x 0.4		V_{CC} x 0.6	V
V_{IL}	Input low voltage	– 0.5		0.2 x V_{CC}	V

6.4 Thermal Information

THERMAL METRIC(1)		SN65DP141 RLJ (WQFN) 38 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	36.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	22.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	10.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	10.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.9	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER CONSUMPTION						
P_{DL}	Device Power dissipation	V_{OD} = Low, V_{CC} = 3.3 V and all 4 channels active		450	625	mW
		V_{OD} = Low, V_{CC} = 2.5 V and all 4 channels active		317	475	mW
P_{DH}	Device Power dissipation	V_{OD} = High, V_{CC} = 3.3 V and all 4 channels active		697	925	mW
		V_{OD} = High, V_{CC} = 2.5 V and all 4 channels active		485	675	mW
P_{DOFF}	Device power with all 4 channels switched off	Refer to I2C section for device configuration		10		mW
CMOS DC SPECIFICATIONS						
I_{IH}	High level input current	V_{IN} = 0.9 × V_{CC}	-40	17	40	µA
I_{IL}	Low level input current	V_{IN} = 0.1 × V_{CC}	-40	17	40	µA
CML INPUTS (IN[3:0]_P, IN[3:0]_N)						
R_{IN}	Differential input resistance	INx_P to INx_N		100		Ω
V_{IN}	Input linear dynamic range	Gain = 0.5		1200		mVpp
V_{ICM}	Input common mode voltage	Internally biased		V_{CC} – 0.8		V
SCD11	Input differential to common mode conversion	100 MHz to 6 GHz		-20		dB
SDD11	Differential input return loss	100 MHz to 6 GHz		-15		dB
CML OUTPUTS (OUT[3:0]_P, OUT[3:0]_N)						
V_{OD}	Output linear dynamic range	R_L = 100 Ω, V_{OD} = HIGH		1200		mVpp
		R_L = 100 Ω, V_{OD} = LOW		600		mVpp
V_{OS}	Output offset voltage	R_L = 100 Ω, 0 V applied at inputs		10		mVpp
V_{OCM}	Output common mode voltage			V_{CC} – 0.4		V
$V_{CM(RIP)}$	Common mode output ripple	K28.5 pattern at 12 Gbps on all 4 channels, No interconnect loss, V_{OD} = HIGH		10	20	mVRMS
$V_{OD(RIP)}$	Differential path output ripple	K28.5 pattern at 12 Gbps on all channels, No interconnect loss, V_{IN} = 1200 mVpp.			20	mVpp

6.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{OC(SS)}$	Change in steady-state common mode output voltage between logic states			±10		mV

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CML OUTPUTS (OUT[3:0]_P, OUT[3:0]_N)						
t_R	Rise time (1)	Input signal with 30 ps rise time, 20% to 80%, See 图 7-3		31		ps
t_F	Fall time (1)	Input signal with 30 ps fall time, 20% to 80%, See 图 7-3		32		ps
SDD22	Differential output return loss	6 GHz (12 Gbps)		-14		dB
		4.05 GHz (HBR3, 8.1 Gbps)		– 9.33		dB
		4.05 GHz (HBR3, 8.1 Gbps)		– 6.35		dB
		1.35 GHz (HBR, 2.7Gbps)		– 3.5		dB
t_{PLH}	Low-to-high propagation delay	See 图 7-2		65		ps
t_{PHL}	High-to-low propagation delay			65		ps
$t_{SK(O)}$	Inter-Pair (lane to lane) output skew (2)	All outputs terminated with 100 Ω, See 图 7-4		8		ps
$t_{SK(PP)}$	Part-to-part skew (3)	All outputs terminated with 100 Ω			50	ps
r_{OT}	Single ended output resistance	Single ended on-chip termination to V_{CC}, Outputs are AC coupled		50		Ω
r_{OM}	Output termination mismatch at 1 MHz	$\Delta r_{OM} = 2 \times \left(\frac{rp - rn}{rn + rp} \right) \times 100$		5%		
	Channel-to-channel isolation	Frequency at 6 GHz	35	45		dB
	Output referred noise(4)	10 MHz to 6 GHz, No other noise source present, V_{OD} = LOW		400		µVRMS
		10 MHz to 6 GHz, No other noise source present, V_{OD} = HIGH		500		µVRMS
EQUALIZATION						
G	At 6 GHz input signal	Equalization Gain, EQ = MAX		15		dB
$V_{(pre)}$	Output pre-cursor pre-emphasis	Input signal with 3.75 pre-cursor and measure it on the output signal, See 图 7-5		3.75		dB
$V_{(pst)}$	Output post-cursor pre-emphasis	Input signal with 12 dB post-cursor and measure it on the output signal, See 图 7-5		12		dB

(1) Rise and Fall measurements include board and channel effects of the test environment, refer to 图 7-1 and 图 7-3.
(2) $t_{SK(O)}$ is the magnitude of the time difference between the channels.
(3) $t_{SK(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same
(4) All noise sources added.

6.7 Switching Characteristics, I²C Interface

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNIT
f_{SCL}	SCL clock frequency			400	KHz
t_{BUF}	Bus free time between START and STOP conditions	1.3			µs
t_{HDSTA}	"Hold time after repeated START condition. After this period, the first clock pulse is generated	0.6			µs
t_{LOW}	Low period of the SCL clock	1.3			µs
t_{HIGH}	High period of the SCL clock	0.6			µs
t_{SUSTA}	Setup time for a repeated START condition	0.6			µs
t_{HDDAT}	Data HOLD time	0			µs
t_{SUDAT}	Data setup time	100			µs
t_R	Rise time of both SDA and SCL signals			300	µs
t_F	Fall time of both SDA and SCL signals			300	µs
t_{SUSTO}	Setup time for STOP condition	0.6			µs

6.8 Typical Characteristics

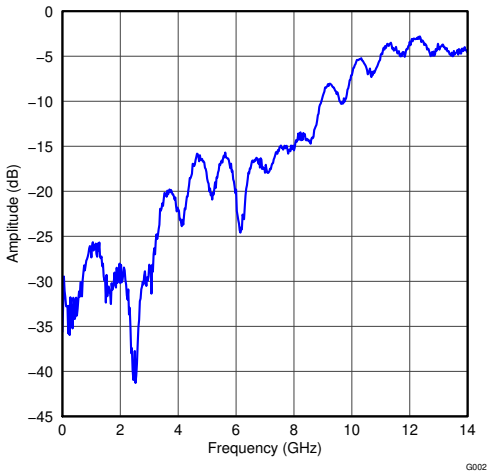


图 6-1. Differential Input Return Loss

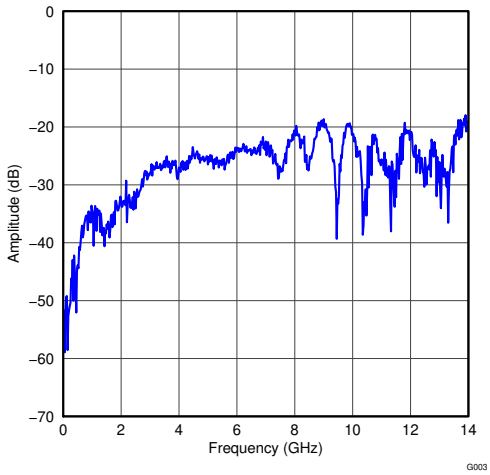


图 6-2. Differential to Common Mode Conversion

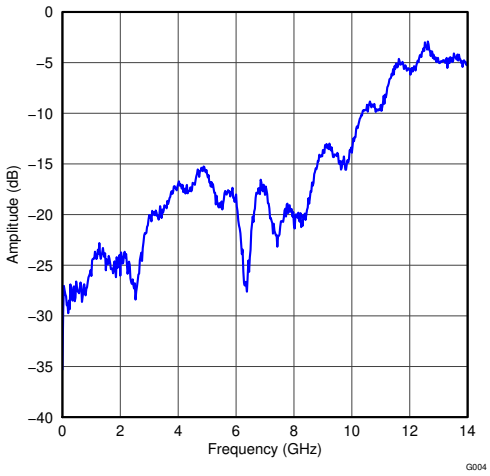


图 6-3. Differential Output Return Loss

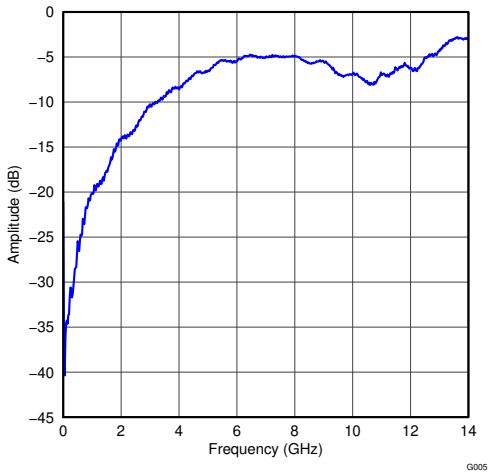


图 6-4. Common Mode Output Return Loss

7 Parameter Measurement Information

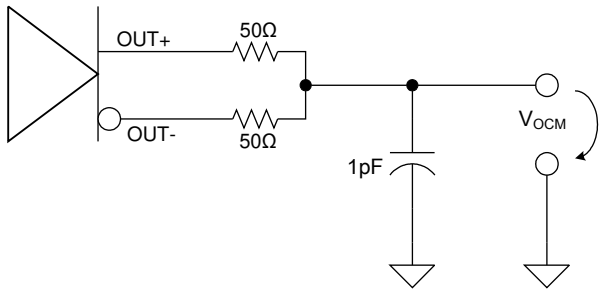


图 7-1. Common Mode Output Voltage Test Circuit

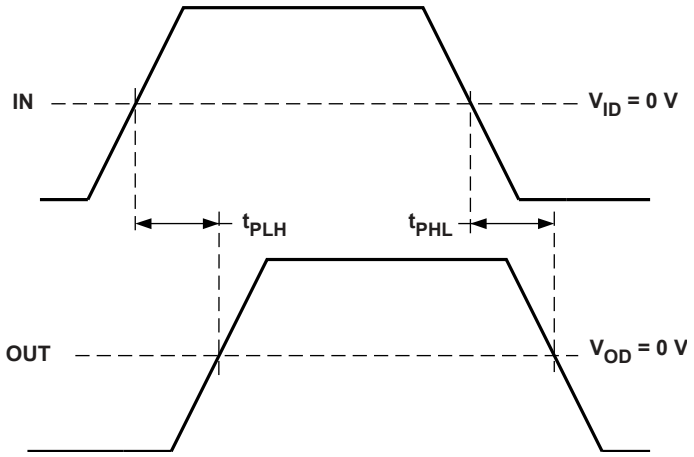


图 7-2. Propagation Delay Input to Output

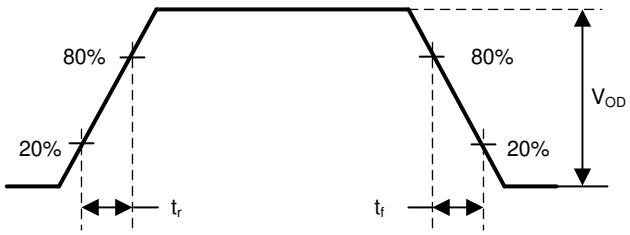


图 7-3. Output Rise and Fall Times

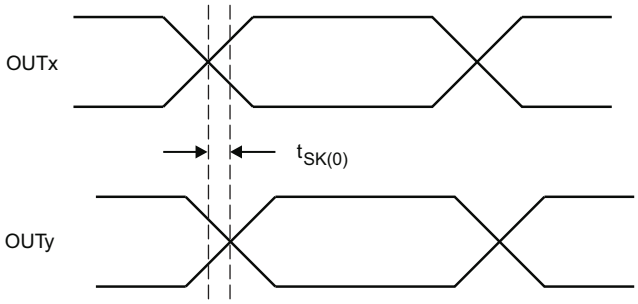


图 7-4. Output Inter-Pair Skew

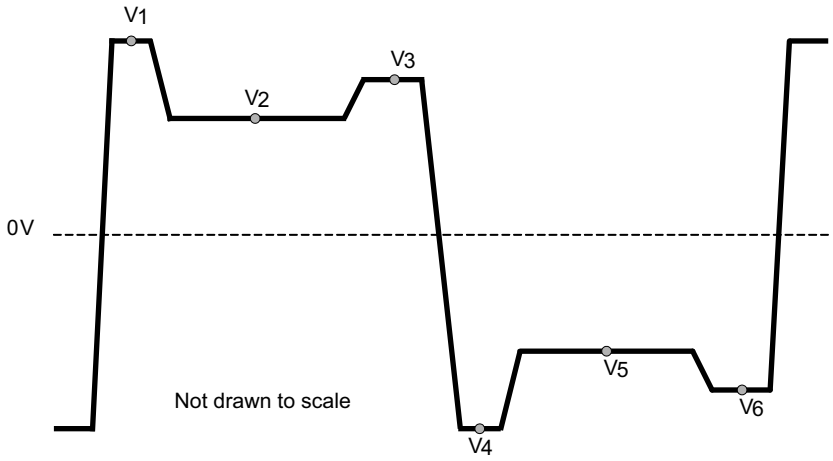


图 7-5. $V_{(pre)}$ and $V_{(post)}$ (test pattern is 1111111100000000 (8-1s, 8-0s))

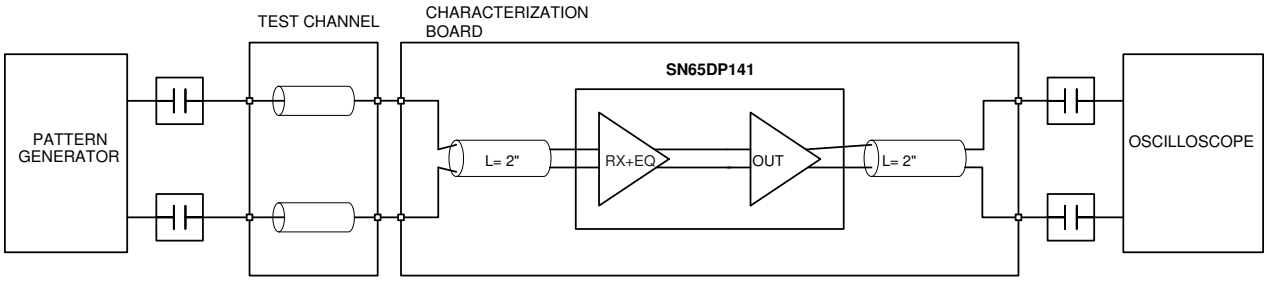


图 7-6. Receive Side Performance Test Circuit

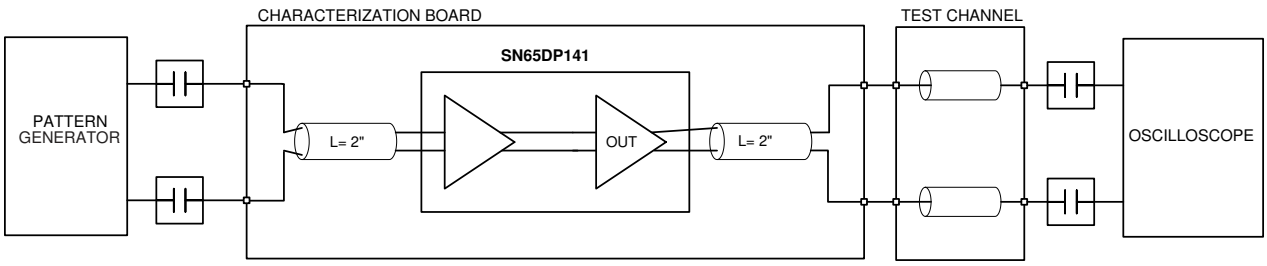


图 7-7. Transmit Side Performance Test Circuit

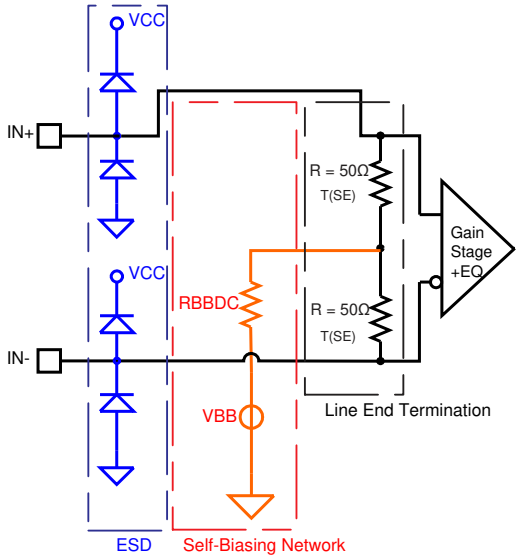


图 7-8. Equivalent Input Circuit

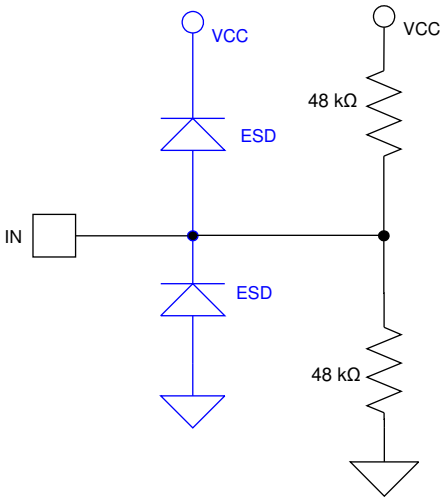


图 7-9. 3-Level Input Biasing Network

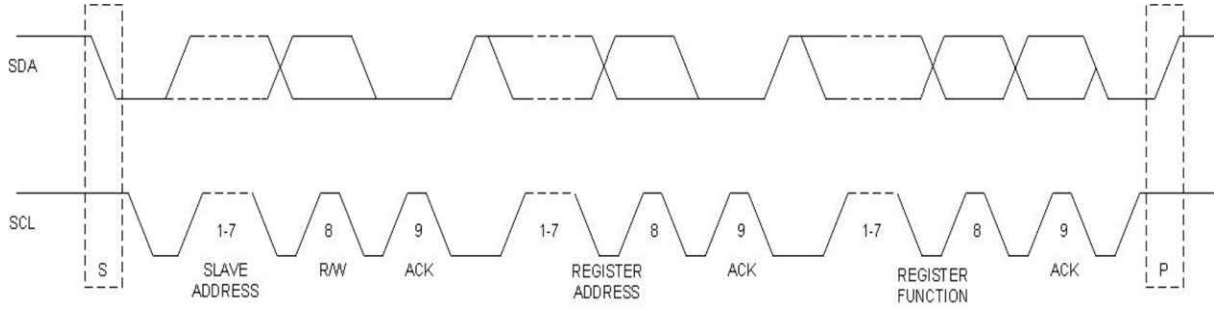


图 7-10. Two – Wire Serial Interface Data Transfer

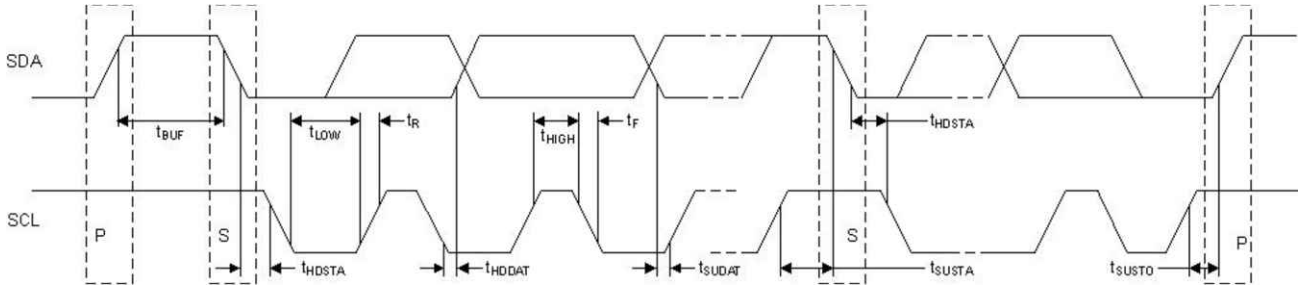


图 7-11. Two – Wire Serial Interface Timing Diagram

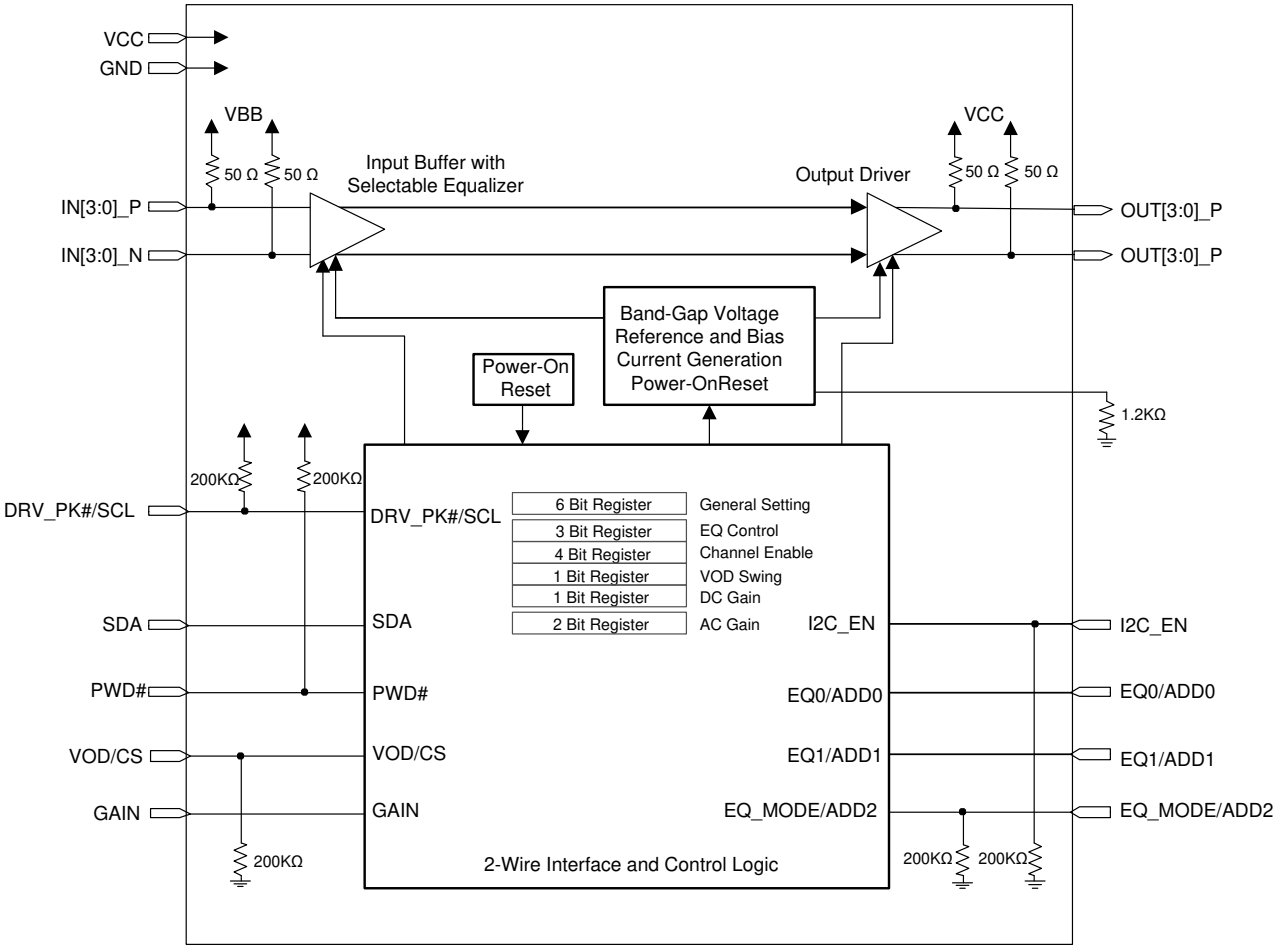
8 Detailed Description

8.1 Overview

The SN65DP141 is an asynchronous, protocol-agnostic, low latency, four-channel linear equalizer optimized for use up to 12 Gbps. The characteristics of this device make it transparent to DisplayPort (DP) link training. It supports all the available DP bit rates from RBR to UHBR10 (1.6 Gbps, 2.7 Gbps, 5.4 Gbps, 8.1 Gbps, and 10.0 Gbps respectively). Additionally, the SN65DP141 is configurable to a trace or cable mode, and hence improves its performance depending on the type of channel it is being used. Its transparency to the DP link training makes the SN65DP141 a position independent device, suitable for source/sink or cable applications, effectively providing a *negative loss* component to the overall link budget, in order to compensate the signal degradation over the channel.

The SN65DP141 is configurable by means of I^2C and GPIOs, allowing independent channel control for activation, equalization, gain, and dynamic range.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 DC and AC Independent Gain Control

Besides the functional block diagram, the behavior of the SN65DP141 can be described as it is shown in 图 8-1; where the input stage first applies a DC gain (0 dB or – 6 dB) and then equalizes the signal, which is driven to the output stage where the SN65DP141 applies an output DC gain (0 dB or 6 dB).

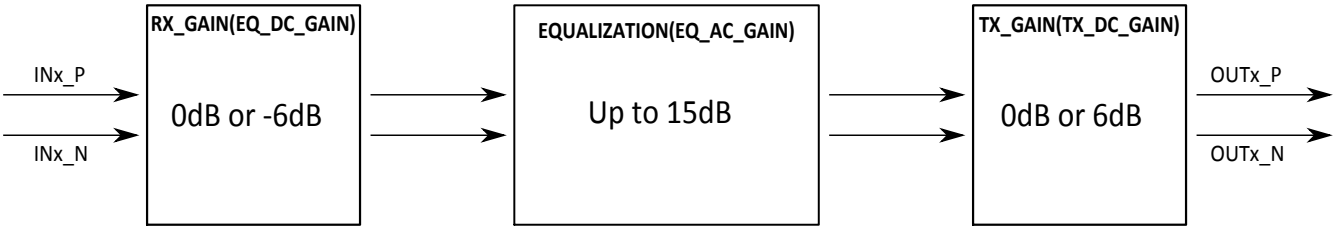


图 8-1. DP141 Signal Chain Gain Control

8.3.2 Two-Wire Serial Interface and Control Logic

The SN65DP141 uses a 2-wire serial interface for digital control. The two circuit inputs, SDA and SCL, are driven, respectively, by the serial data and serial clock from a microcontroller, for example. The SDA and SCK pins require external 10 kΩ pull-ups to VCC.

The 2-wire interface allows write access to the internal memory map to modify control registers and read access to read out control and status signals. The SN65DP141 is a slave device only which means that it cannot initiate a transmission itself; it always relies on the availability of the SCK signal for the duration of the transmission. The master device provides the clock signal as well as the START and STOP commands. The protocol for a data transmission is as follows:

1. START command
2. 7 bit slave address (0000ADD [2:0]) followed by an eighth bit which is the data direction bit (R/W). A zero indicates a WRITE and a 1 indicates a READ. The ADD [2:0] address bits change with the status of the ADD2, ADD1, and ADD0 device pins, respectively. If the pins are left floating or pulled down, the 7 bit slave address is 0000000.
3. 8-bit register address
4. 8-bit register data word
5. STOP command

Regarding timing, the SN65DP141 is I^2C compatible. The typical timing is shown in 图 7-11 and a complete data transfer is shown in 图 7-10. Parameters for these figures are defined in the I^2C Interface section of the *Switching Characteristics*.

8.3.3 Bus Idle

Both SDA and SCL lines remain HIGH

8.3.4 Start Data Transfer

A change in the state of the SDA line, from HIGH to LOW, while the SCL line is HIGH, defines a START condition (S). Each data transfer is initiated with a START condition.

8.3.5 Stop Data Transfer

A change in the state of the SDA line from LOW to HIGH while the SCL line is HIGH defines a STOP condition (P). Each data transfer is terminated with a STOP condition; however, if the master still wishes to communicate on the bus, it can generate a repeated START condition and address another slave without first generating a STOP condition.

8.3.6 Data Transfer

The number of data bytes transferred between a START and a STOP condition is not limited and is determined by the master device. The receiver acknowledges the transfer of data.

8.3.7 Acknowledge

Each receiving device, when addressed, is obliged to generate an acknowledge bit. The transmitter releases the SDA line and a device that acknowledges must pull down the SDA line during the acknowledge clock pulse in such a way that the SDA line is stable LOW during the HIGH period of the acknowledge clock pulse. Setup and hold times must be taken into account. When a slave-receiver doesn't acknowledge the slave address, the data line must be left HIGH by the slave. The master can then generate a STOP condition to abort the transfer. If the slave-receiver does acknowledge the slave address but some time later in the transfer cannot receive any more data bytes, the master must abort the transfer. This is indicated by the slave generating the not acknowledge on the first byte to follow. The slave leaves the data line HIGH and the master generates the STOP condition.

8.4 Device Functional Modes

8.4.1 TRACE and CABLE Equalization Modes

The SN65DP141 is optimized for both trace and cable application at its input. The device pin EQ_MODE sets the EQ gain curve profile suitable for these two use cases.

8.4.2 Control Modes

The SN65DP141 features two control modes: GPIO and I2C, and the selection between these two modes is by means of the I2C_EN terminal, which activates the GPIO when tied to LOW; otherwise, the I2C mode is active due to its internal pull-up resistance.

8.4.3 GPIO MODE

Device Pins RX_GAIN, EQ1 and EQ0 determines receiver DC and AC gain as shown in 表 8-1 and 表 8-2.

表 8-1. EQ Pin Settings

EQ1	EQ0	EQ Setting
GND	GND	000
GND	HiZ	000
GND	VCC	001
HiZ	GND	010
HiZ	HiZ	011
HiZ	VCC	100
VCC	GND	101
VCC	HiZ	110
VCC	VCC	111

表 8-2. RX DC and AC GAIN Settings

EQ Configuration		EQ Gain	
EQ Setting	RX_GAIN	EQ_DC_GAIN (dB)	EQ_AC_GAIN (dB)
000 - 111	LOW	–6	1 - 9
000 - 111	HiZ	–6	7 - 17
000 - 111	HIGH	0	1 - 9

8.4.4 I²C Mode

表 8-3. I2C Control Settings Description for RX DC and AC GAIN

EQ_MODE	EQ_DC GAIN	RX_GAIN<1:0>	EQ_Setting<2:0>	DC GAIN (dB)	AC GAIN (dB)	APPLICATION
0	0	00	000 to 111	-6	1 to 9	Short Input Cable; Large Input Swing
		11	000 to 111	-6	7 to 17	Long Input Cable; Large Input Swing
	1	01	000 to 111	0	1 to 9	Short Input Cable; Small Input Swing
		11	000 to 111	0	2 to 10	Short Input Cable, Small Input Swing
1	0	00	000 to 111	-6	1 to 9	Short Input Trace; Large Input Swing
		11	000 to 111	-6	7 to 17	Long Input Trace; Large Input Swing
	1	01	000 to 111	0	1 to 9	Short Input Trace; Small Input Swing
		11	000 to 111	0	2 to 10	Short Input Trace, Small Input Swing

8.5 Register Maps

8.5.1 Register 0x00 (General Device Settings) (offset = 00000000) [reset = 00000000]

图 8-2. Register 0x00 (General Device Settings)

7	6	5	4	3	2	1	0
SW_GPIO	PWRDOWN	SYNC_01	SYNC_23	SYNC_ALL	EQ_MODE		RSVD
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-4. Register 0x00 (General Device Settings)

Bit	Field	Type	Reset	Description
7	SW_GPIO	R/W	0	Switching logic is controlled by GPIO or I2C: 0 = I2C control 1 = GPIO control
6	PWRDOWN	R/W	0	Power down the device: 0 = Normal operation 1 = Powerdown
5	SYNC_01	R/W	0	All settings from channel 1 will be used for channel 0 and 1: 0 = Channel 0 tracking channel 1 settings 1 = No tracking tracking
4	SYNC_ 23	R/W	0	All settings from channel 2 will be used for channel 2 and 3: 0 = Channel 3 tracking channel 2 settings 1 = No channel tracking
3	SYNC_ALL	R/W	0	All settings from channel 1 will be used on all channels: 0 = All channels tracking channel 1 1 = No channel tracking Overwrites SYNC_01 and SYNC_23
2	EQ_MODE	R/W	0	Set EQ mode: 0 = Cable mode 1 = Trace mode
1		R/W	0	
0	RSVD	R/W	0	For TI use only

8.5.2 Register 0x01 (Channel Enable) (offset = 00000000) [reset = 00000000]

图 8-3. Register 0x01 (Channel Enable)

7	6	5	4	3	2	1	0
				LN_EN_CH3	LN_EN_CH2	LN_EN_CH1	LN_EN_CH0
R	R	R	R	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-5. Register 0x01 (Channel Enable)

Bit	Field	Type	Reset	Description
7		R	0	
6		R	0	
5		R	0	
4		R	0	
3	LN_EN_CH3	R/W	0	Channel 3 enable: 0 = Enable 1 = Disable
2	LN_EN_CH2	R/W	0	Channel 3 enable: 0 = Enable 1 = Disable
1	LN_EN_CH1	R/W	0	Channel 1 enable: 0 = Enable 1 = Disable
0	LN_EN_CH0	R/W	0	Channel 0 enable: 0 = Enable 1 = Disable

8.5.3 Register 0x02 (Channel 0 Control Settings) (offset = 00000000) [reset = 00000000]

图 8-4. Register 0x02 (Channel 0 Control Settings)

7	6	5	4	3	2	1	0
RSVD	EQ Setting<2>	EQ Setting<1>	EQ Setting<0>	TX_GAIN	EQ_DC_GAIN	RX_GAIN<1>	RX_GAIN<0>
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-6. Register 0x02 (Channel 0 Control Settings)

Bit	Field	Type	Reset	Description
7	RSVD	R/W	0	
6	EQ Setting<2>	R/W	0	Equalizer adjustment setting: 000 = Minimum equalization setting 111 = Maximum equalization setting
5	EQ Setting<1>	R/W	0	
4	EQ Setting<0>	R/W	0	
3	TX GAIN	R/W	0	Channel [0] TX_DC_GAIN control: 0 = Set 0 dB DC gain for transmitter 1 = Set 6 dB DC gain for transmitter
2	EQ_DC_GAIN	R/W	0	Channel [0] EQ DC gain: 0 = Set EQ DC gain to -6 dB 1 = Set EQ DC gain to -0 dB
1	RX_GAIN<1>	R/W	0	Equivalent to RX_GAIN control pin for channel [0]. 00: RX_GAIN = Low 01: RX_GAIN = HiZ 11: RX_GAIN = High
0	RX_GAIN<0>	R/W	0	

8.5.4 Register 0x03 (Channel 0 Enable Settings) (offset = 00000000) [reset = 00000000]

图 8-5. Register 0x03 (Channel 0 Enable Settings)

7	6	5	4	3	2	1	0
					DRV_PEAK	EQ_EN	DRV_EN
R	R	R	R	R	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-7. Register 0x03 (Channel 0 Enable Settings)

Bit	Field	Type	Reset	Description
7		R	0	
6		R	0	
5		R	0	
4		R	0	
3		R	0	
2	DRV_PEAK	R/W	0	Channel [0] driver peaking: 0 = Disables driver Peaking 1 = Enables driver 6 db AC Peaking"
1	EQ_EN	R/W	0	Channel [0] EQ stage enable: 0 = Enable 1 = Disable
0	RSVDRV_EN	R/W	0	Channel [0] driver stage enable: 0 = Enable 1 = Disable

8.5.5 Register 0x05 (Channel 1 Control Settings) (offset = 00000000) [reset = 00000000]

图 8-6. Register 0x05 (Channel 1 Control Settings)

7	6	5	4	3	2	1	0
RSVD	EQ Setting<2>	EQ Setting<1>	EQ Setting<0>	TX_GAIN	EQ_DC_GAIN	RX_GAIN<1>	RX_GAIN<0>
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-8. Register 0x05 (Channel 1 Control Settings)

Bit	Field	Type	Reset	Description
7	RSVD	R/W	0	
6	EQ Setting<2>	R/W	0	Equalizer adjustment setting: 000 = Minimum equalization setting 111 = Maximum equalization setting
5	EQ Setting<1>	R/W	0	
4	EQ Setting<0>	R/W	0	
3	TX_GAIN	R/W	0	Channel [1] TX_DC_GAIN control: 0 = Set 0 dB DC gain for transmitter 1 = Set 6 dB DC gain for transmitter
2	EQ_DC_GAIN	R/W	0	Channel [1] EQ DC gain: 0 = Set EQ DC gain to -6 dB 1 = Set EQ DC gain to -0 dB
1	RX_GAIN<1>	R/W	0	Equivalent to RX_GAIN control pin for channel [1]. 00: RX_GAIN = Low 01: RX_GAIN = HiZ 11: RX_GAIN = High
0	RX_GAIN<0>	R/W	0	

8.5.6 Register 0x06 (Channel 1 Enable Settings) (offset = 00000000) [reset = 00000000]

图 8-7. Register 0x06 (Channel 1 Enable Settings)

7	6	5	4	3	2	1	0
					DRV_PEAK	EQ_EN	DRV_EN
R	R	R	R	R	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-9. Register 0x06 (Channel 1 Enable Settings)

Bit	Field	Type	Reset	Description
7		R	0	
6		R	0	
5		R	0	
4		R	0	
3		R	0	
2	DRV_PEAK	R/W	0	Channel [1] driver peaking: 0 = Disables driver Peaking 1 = Enables driver 6 db AC Peaking
1	EQ_EN	R/W	0	Channel [1] EQ stage enable: 0 = Enable 1 = Disable
0	DRV_EN	R/W	0	Channel [1] driver stage enable: 0 = Enable 1 = Disable

8.5.7 Register 0x08 (Channel 2 Control Settings) (offset = 00000000) [reset = 00000000]

图 8-8. Register 0x08 (Channel 2 Control Settings)

7	6	5	4	3	2	1	0
RSVD	EQ Setting<2>	EQ Setting<1>	EQ Setting<0>	TX_GAIN	EQ_DC_GAIN	RX_GAIN<1>	RX_GAIN<0>
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-10. Register 0x08 (Channel 2 Control Settings)

Bit	Field	Type	Reset	Description
7	RSVD	R/W	0	
6	EQ Setting<2>	R/W	0	Equalizer adjustment setting: 000 = Minimum equalization setting 111 = Maximum equalization setting
5	EQ Setting<1>	R/W	0	
4	EQ Setting<0>	R/W	0	
3	TX_GAIN	R/W	0	Channel [2] TX_DC_GAIN control: 0 = Set 0 dB DC gain for transmitter 1 = Set 6 dB DC gain for transmitter
2	EQ_DC_GAIN	R/W	0	Channel [2] EQ DC gain: 0 = Set EQ DC gain to -6 dB 1 = Set EQ DC gain to -0 dB
1	RX_GAIN<1>	R/W	0	Equivalent to RX_GAIN control pin for channel [2]. 00: RX_GAIN = Low 01: RX_GAIN = HiZ 11: RX_GAIN = High
0	RX_GAIN<0>	R/W	0	

8.5.8 Register 0x09 (Channel 2 Enable Settings) (offset = 00000000) [reset = 00000000]

图 8-9. Register 0x09 (Channel 2 Enable Settings)

7	6	5	4	3	2	1	0
					DRV_PEAK	EQ_EN	DRV_EN
R	R	R	R	R	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-11. Register 0x09 (Channel 2 Enable Settings)

Bit	Field	Type	Reset	Description
7		R	0	
6		R	0	
5		R	0	
4		R	0	
3		R	0	
2	DRV_PEAK	R/W	0	Channel [2] driver peaking: 0 = Disables driver Peaking 1 = Enables driver 6 db AC Peaking
1	EQ_EN	R/W	0	Channel [2] driver stage enable: 0 = Enable 1 = Disable
0	DRV_EN	R/W	0	Channel [2] driver stage enable: 0 = Enable 1 = Disable

8.5.9 Register 0x0B (Channel 3 Control Settings) (offset = 00000000) [reset = 00000000]

图 8-10. Register 0x0B (Channel 3 Control Settings)

7	6	5	4	3	2	1	0
RSVD	EQ Setting<2>	EQ Setting<1>	EQ Setting<0>	TX_GAIN	EQ_DC_GAIN	RX_GAIN<1>	RX_GAIN<0>
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-12. Register 0x0B (Channel 3 Control Settings)

Bit	Field	Type	Reset	Description
7	RSVD	R/W	0	
6	EQ Setting<2>	R/W	0	Equalizer adjustment setting: 000 = Minimum equalization setting 111 = Maximum equalization setting
5	EQ Setting<1>	R/W	0	
4	EQ Setting<0>	R/W	0	
3	TX_GAIN	R/W	0	Channel [3] TX_DC_GAIN control: 0 = Set 0 dB DC gain for transmitter 1 = Set 6 dB DC gain for transmitter
2	EQ_DC_GAIN	R/W	0	Channel [3] EQ DC gain: 0 = Set EQ DC gain to -6 dB 1 = Set EQ DC gain to -0 dB
1	RX_GAIN<1>	R/W	0	Equivalent to RX_GAIN control pin for channel [3]. 00: RX_GAIN = Low 01: RX_GAIN = HiZ 11: RX_GAIN = High
0	RX_GAIN<0>	R/W	0	

8.5.10 Register 0x0C (Channel 3 Control Settings) (offset = 00000000) [reset = 00000000]

图 8-11. Register 0x0C (Channel 3 Enable Settings)

7	6	5	4	3	2	1	0
					DRV_PEAK	EQ_EN	DRV_EN
R	R	R	R	R	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

表 8-13. Register 0x0C (Channel 3 Enable Settings)

Bit	Field	Type	Reset	Description
7		R	0	
6		R	0	
5		R	0	
4		R	0	
3		R	0	
2	DRV_PEAK	R/W	0	Channel [3] driver peaking: 0 = Disables driver Peaking 1 = Enables driver 6db AC Peaking
1	EQ_EN	R/W	0	Channel [3] EQ stage enable: 0 = Enable 1 = Disable
0	RSVDRV_EN	R/W	0	Channel [3] driver stage enable: 0 = Enable 1 = Disable

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The SN65DP141 can be used in Source, Sink, cable, and dongle applications, where the device is transparent to the DisplayPort link layer. For illustrating purposes, this section shows the implementation of a DisplayPort dongle, 图 9-1 shows an example of the SN65DP141 on a dongle board, where the AUX channel is directly connected from source to sink, meanwhile the power can be provided either way from the DP source or an external power source.

9.2 Typical Application

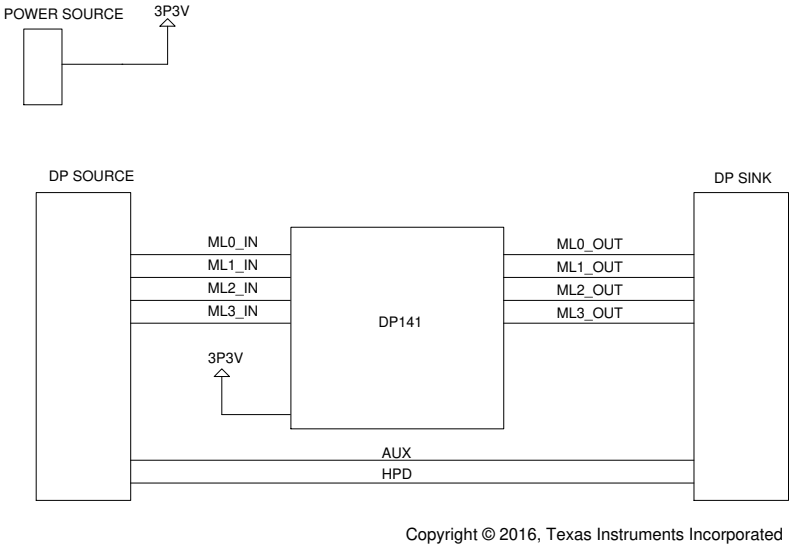


图 9-1. SN65DP141 Application Diagram

9.2.1 Design Requirements

The SN65DP141 can be designed into many types of applications. All applications have certain requirements for the system to work properly. The voltage rails are required to support the lowest possible power consumption. Configure the device by using I2C. The GPIO configuration is provided as I^2C is not available in all cases. Because sources may have different naming conventions, confirm the link between source and sink is correctly mapped through the SN65DP141.

表 9-1. Design Parameters

PARAMETER	VALUE
Operating data rate	UHBR10 (10 Gbps)
Supply voltage	3.3 V
Main link input voltage	V_{ID} = 75 mVpp to 1.2 Vpp
Control pin Low	1 KΩ pulled to GND
Control pin Mid	No Connect
Control pin Low	1 KΩ pulled to High
Main link AC decoupling capacitor	75 to 200 nF, recommend 100 nF

First approach for GAIN configuration: It is highly recommend that DC GAIN be set to 1, this leads the output to preserve the input amplitude (GAIN = 1):

- For GPIO implementation: Use a pull-up resistor on the GAIN terminal (pin 36), refer to the schematic in 图 9-2.
- For I²C implementation: write a 1 to the bit 2 of the registers 0x02, 0x05, 0x08 and 0x0B. Refer to 节 *8.3.2* for a detailed description of the I²C interface

9.2.2 Detailed Design Procedure

Designing in the SN65DP141 requires the following:

- Determine the loss profile on the DP input and output channels and cables.
- Based upon the loss profile and signal swing, determine the optimal configuration for the SN65DP141, to pass electrical compliance (Equalization mode, EQ Gain, DC gain, and AC Gain).
- See 图 9-2 for information on using the AC coupling capacitors and control pin resistors, as well as for recommended decouple capacitors from VCC pins to ground.
- Configure the TheSN65DP141 using the GPIO terminals or the I²C interface:
  - GPIO – Using the terminals EQ_MODE, EQ1, EQ1, and gain.
  - I²C – Refer to the I2C *Register Maps* and the *Two-Wire Serial Interface and Control Logic* sections for a detailed configuration procedures.
- The thermal pad must be connected to ground.

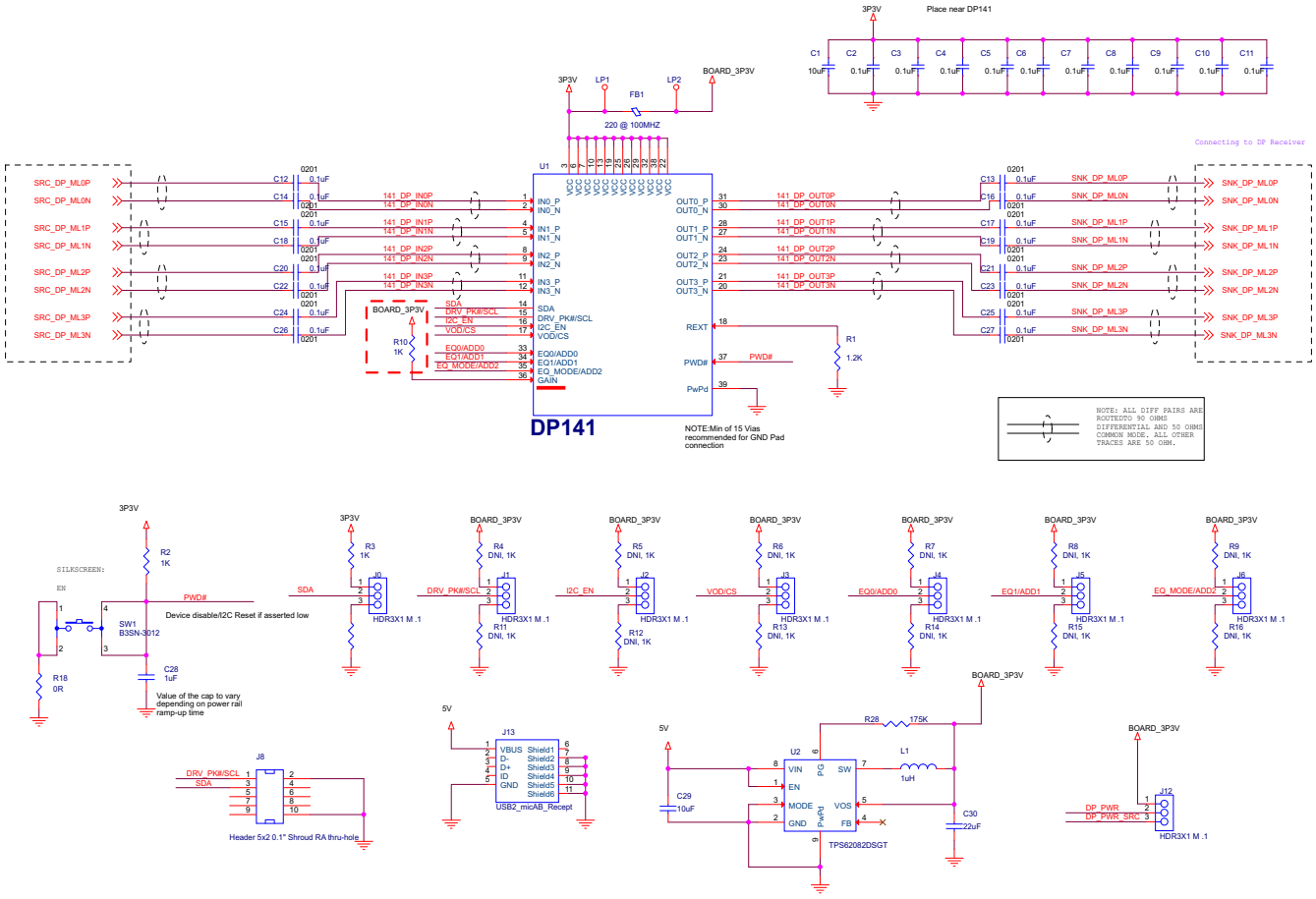
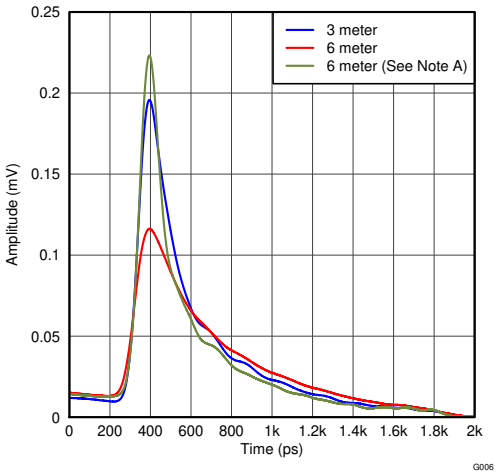


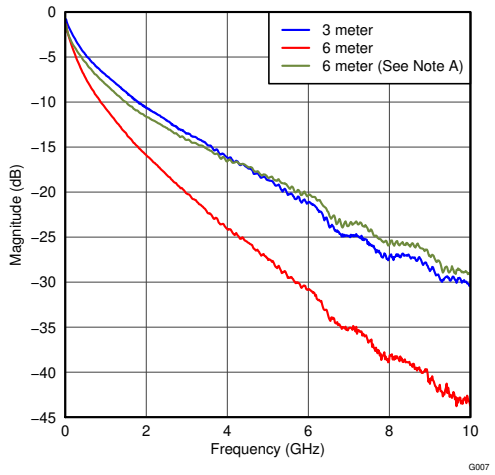
图 9-2. SN65DP141 Application Schematic

9.2.3 Application Curves



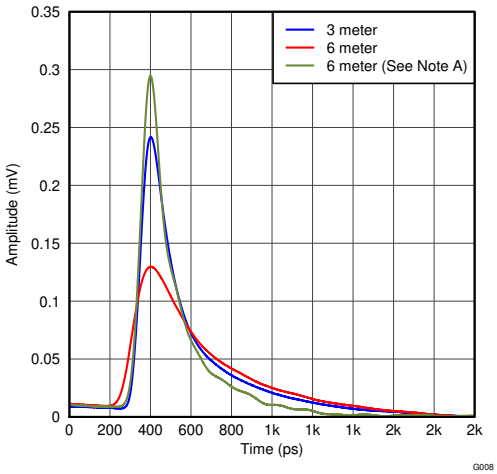
With SN65DP141 -> EQ = 4, VOD = High, ACGain = HiZ, DCGain = Low

图 9-3. Cable Mode – Symbol Response



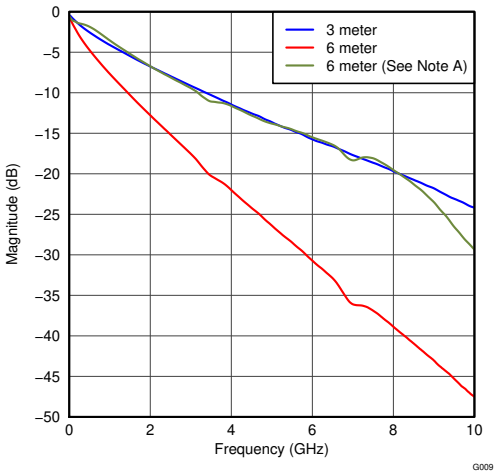
With SN65DP141 -> EQ = 4, VOD = High, ACGain = HiZ, DCGain = Low

图 9-4. Cable Mode – Frequency Domain



With SN65DP141 -> EQ = 7, VOD = High, ACGain = High, DCGain = Low

图 9-5. Trace Mode – Symbol Response



With SN65DP141 -> EQ = 7, VOD = High, ACGain = High, DCGain = Low

图 9-6. Trace Mode – Frequency Domain

10 Power Supply Recommendations

To minimize the power supply noise floor, provide good decoupling near the SN65DP141 power pins. It is recommended to place one 0.01-μF ceramic capacitor at each power pin, and two 0.1-μF ceramic capacitors on each power node. The distance between the SN65DP141 and capacitors should be minimized to reduce loop inductance and provide optimal noise filtering. Placing the capacitor underneath the SN65DP141 on the bottom of the PCB is often a good choice. A 100-pF ceramic capacitor can be put at each power pin to optimize the EMI performance.

11 Layout

11.1 Layout Guidelines

- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.
- If an additional supply voltage plane or signal layer is needed, add a second power/ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high frequency bypass capacitance significantly.
- The control pin pull-up and pull-down resistors are shown in application section for reference. If a high level is needed then only uses the pull up. If a low level is needed only use the pull down.
- Place passive components within the signal path, such as source-matching resistors or ac-coupling capacitors, next to each other. Routing as in case a) creates wider trace spacing than in b); the resulting discontinuity, however, is limited to a far narrower area.
- When routing traces next to a via or between an array of vias, make sure that the via clearance section does not interrupt the path of the return current on the ground plane below.
- Avoid metal layers and traces underneath or between the pads off the DisplayPort connectors for better impedance matching. Otherwise they will cause the differential impedance to drop below 75 Ω and fail the board during TDR testing.
- Use solid power and ground planes for 100 Ω impedance control and minimum power noise.
- For a multi-layer PCB, it is recommended to keep one common GND layer underneath the device and connect all ground terminals directly to this plane. For 100 Ω differential impedance, use the smallest trace spacing possible, which is usually specified by the PCB vendor.
- Keep the trace length as short as possible to minimize attenuation.
- Place bulk capacitors (that is, 10 μF) close to power sources, such as voltage regulators or where the power is supplied to the PCB.

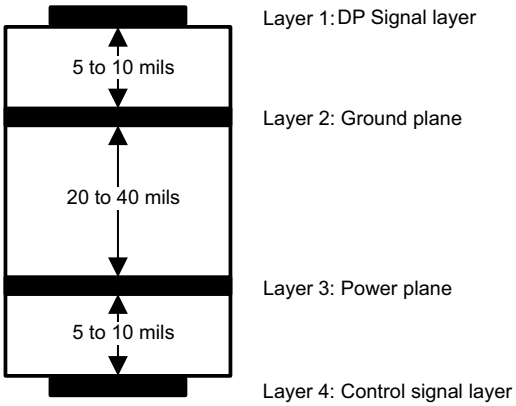


图 11-1. PCB Stack

11.2 Layout Example

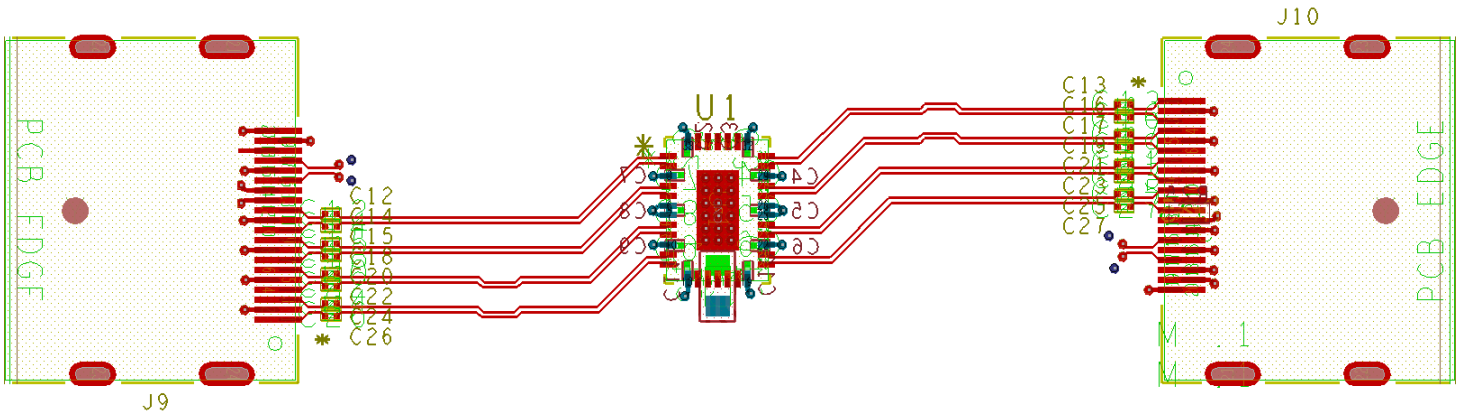


图 11-2. Example Layout (Top)

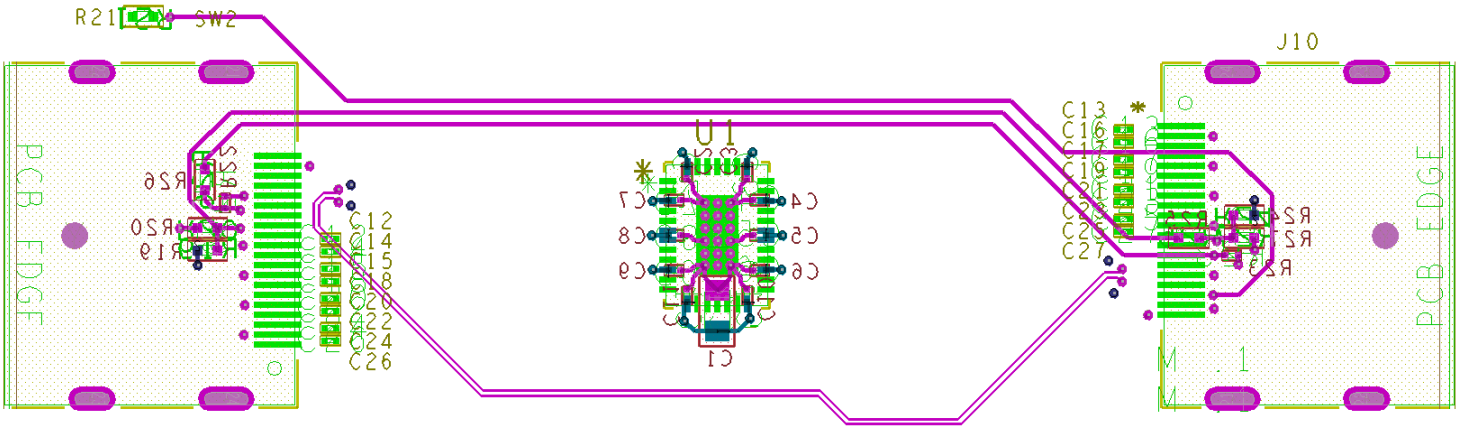


图 11-3. Example Layout (Top)

12 Device and Documentation Support

12.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

12.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65DP141RLJR	ACTIVE	WQFN	RLJ	38	3000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	DP141	Samples
SN65DP141RLJT	ACTIVE	WQFN	RLJ	38	250	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	DP141	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

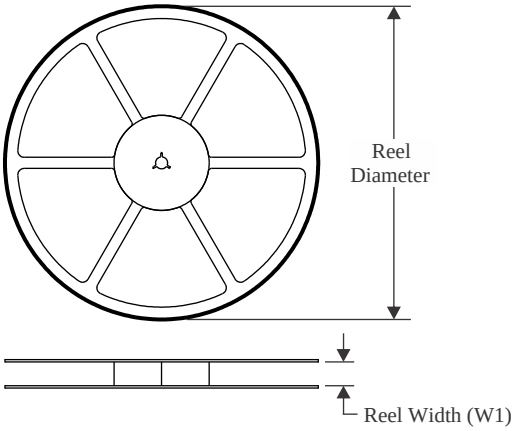
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

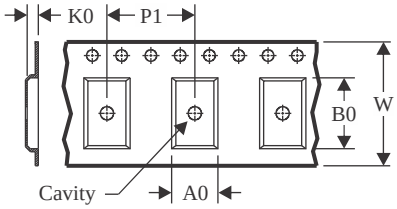
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

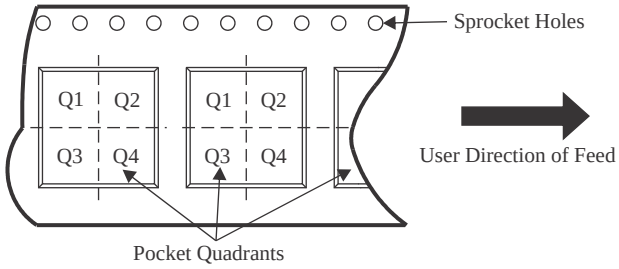


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

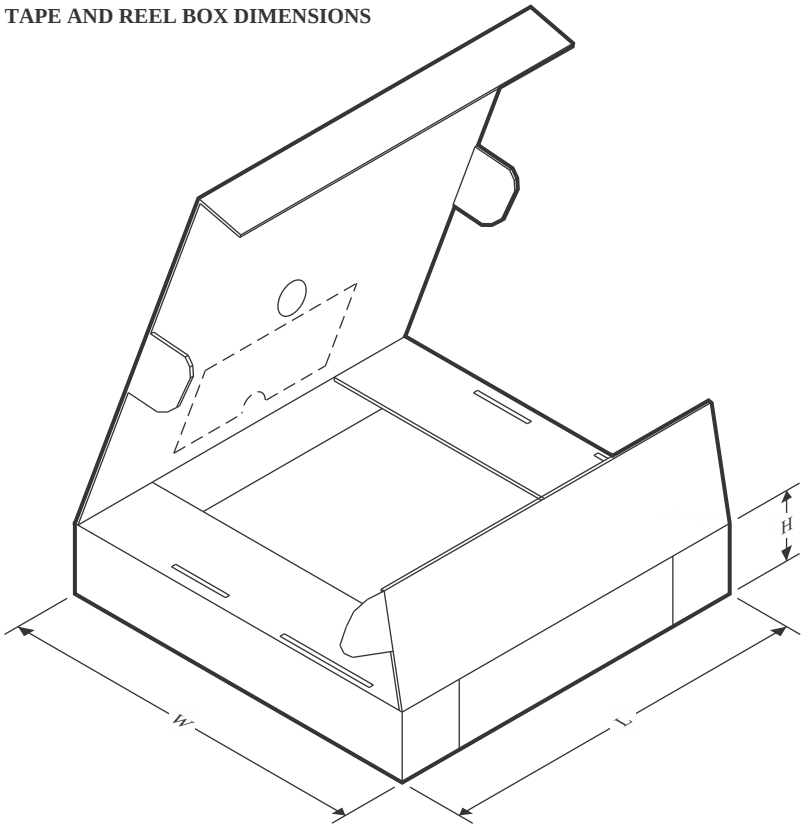
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65DP141RLJR	WQFN	RLJ	38	3000	330.0	16.4	5.25	7.25	1.45	8.0	16.0	Q1
SN65DP141RLJT	WQFN	RLJ	38	250	330.0	16.4	5.25	7.25	1.45	8.0	16.0	Q1

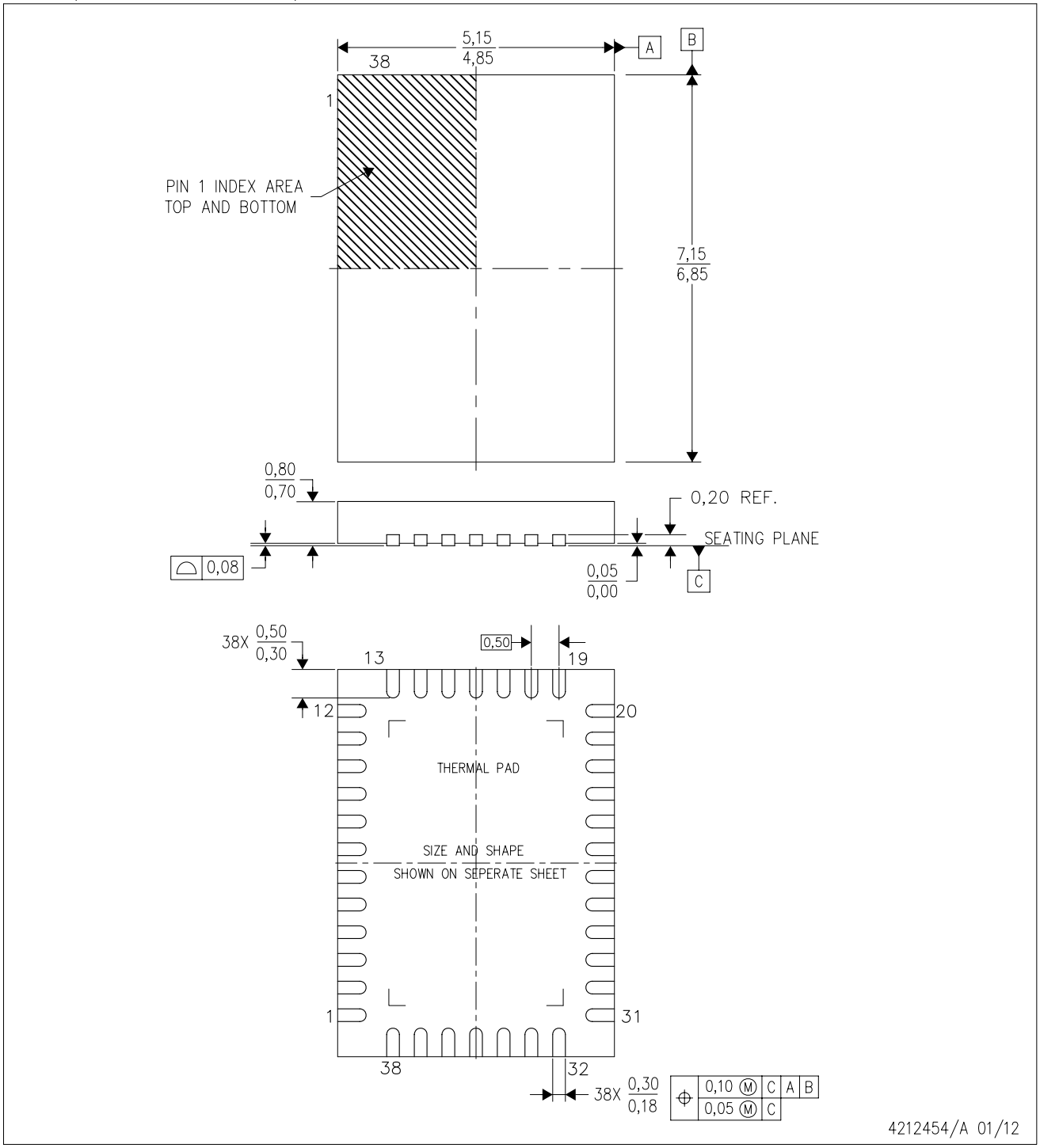
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65DP141RLJR	WQFN	RLJ	38	3000	367.0	367.0	38.0
SN65DP141RLJT	WQFN	RLJ	38	250	367.0	367.0	38.0

RLJ (R–PWQFN–N38) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5–1994.
B. This drawing is subject to change without notice.
C. Quad Flatpack, No–leads (QFN) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Falls within JEDEC MO–220.

重要声明和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265